

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**Patent Number:** 6,797,591

**Issued:** 09/28/2004

**Name of Patentee:** Gormley et al.

**Title of Invention:** METHOD FOR FORMING A SEMICONDUCTOR DEVICE AND A  
SEMICONDUCTOR DEVICE FORMED BY THE METHOD

**Attention Certificate of Corrections Branch**  
**Commissioner for Patents**  
**P.O. Box 1450**  
**Alexandria, VA 22313-1450**

**SUPPLEMENTAL REQUEST FOR CERTIFICATE OF CORRECTION  
OF PATENT FOR PTO MISTAKE (37 CFR 1.322(a))**

1. Attached, in duplicate, is Form PTO-1050, with at least one copy being suitable for printing.
2. The exact page and line number where the errors are shown correctly in the application file are:

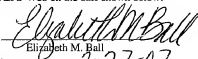
Page 18, line 18

Page 19, line 9, 20

Page 21, line 3

Claim 38 as amended in an amendment mailed 1/24/03

I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with the United States Patent and Trademark Office, via EFS-Web on the date shown below.

  
Elizabeth M. Ball  
Date: 2-27-07

3. Please send the Certificate to:

Name: Matthew E. Connors

Address: Gauthier & Connors, LLP

225 Franklin Street, Suite 2300

Boston, Massachusetts 02110

Reg. No.:33,298

SIGNATURE OF ATTORNEY

A handwritten signature in cursive script, appearing to read "Matthew E. Connors", written over a horizontal line.

Matthew E. Connors  
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## UNITED STATES PATENT AND TRADEMARK OFFICE CERTIFICATE OF CORRECTION

PATENT NO. : 6,797,591

DATED : 09/28/04

INVENTOR(S) : Gormley et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In Column 10, claim 10, line 64, delete "second stop layer being bonded to the one of the second and" and replace with "second etch stop layer being bonded to the one of the second and"

In Column 11, claim 17, line 18, delete "16" and replace with "15"

In Column 11, claim 20, line 30, delete " second and third layers and of semiconductor material." and replace with " second and third layers are of semiconductor material."

In Column 12, claim 31, line 23, delete the word "each" and insert the word "etch"

In Column 12, claim 38, line 48 , delete "first layer is at least half the area of the component in plan" and insert "first layer adjacent the component is at least half the area of the component in plan"

MAILING ADDRESS OF SENDER:

Gauthier & Connors LLP  
225 Franklin Street Suite 2300  
Boston, MA 02110

PATENT NO. 6,797,591

No. of additional copies

⇒ 1 of 1

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

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